

	Hits	Search Text	DBs
23	3	((substrate or wafer) same ((tetracarboxylic near2 dianhydride) or \$4dioxatricyclo\$6dodecane\$6tetraone) same ((alicyclic near3 diamine) or diaminocyclohexane or isophoronediamine or bisaminomethylcyclohexane)) and (expos\$3 or imaging or irradiat\$4 or illuminat\$4 or pattern\$4) and ((dielectric or TiO or TiN or SiN) same (substrate or wafer)) and ((metal\$4 or conductive or wir\$3) same (pattern or cavity or line)) and ((develop\$4 or strip\$4 or remov\$3) same (polymer or photoresist or resist or polyimide or polyamide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
24	5	((tetracarboxylic near2 dianhydride) or \$4dioxatricyclo\$6dodecane\$6tetraone) same ((alicyclic near3 diamine) or diaminocyclohexane or isophoronediamine or bisaminomethylcyclohexane)) and (expos\$3 or imaging or irradiat\$4 or illuminat\$4 or pattern\$4) and ((dielectric or TiO or TiN or SiN) same (substrate or wafer)) and ((metal\$4 or conductive or wir\$3) same (pattern or cavity or line)) and ((develop\$4 or strip\$4 or remov\$3) same (polymer or photoresist or resist or polyimide or polyamide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
25	3	430/322.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
26	3	430/324.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
27	3	430/325.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
28	3	430/270.1.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
29	4	"430"/\$.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)	USOCR
30	4	((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)	USOCR

	Hit s	Search Text	DBs
31	1	(((tetracarboxylic near2 dianhydride) or \$4dioxatricyclo\$6dodecane\$6tetraone) same ((alicyclic near3 diamine) or diaminocyclohexane or isophoronediamine or bisaminomethylcyclohexane)) and (expos\$3 or imaging or irradiat\$4 or illuminat\$4 or pattern\$4) and ((dielectric or TiO or TiN or SiN) same (substrate or wafer)) and ((metal\$4 or conductive or wir\$3) same (pattern or cavity or line)) and ((develop\$4 or strip\$4 or remov\$3) same (polymer or photoresist or resist or polyimide or polyamide))).clm.	US-PGPUB
32	1	(((tetracarboxylic near2 dianhydride) or \$4dioxatricyclo\$6dodecane\$6tetraone) same ((alicyclic near3 diamine) or diaminocyclohexane or isophoronediamine or bisaminomethylcyclohexane)) and (expos\$3 or imaging or irradiat\$4 or illuminat\$4 or pattern\$4) and ((dielectric or TiO or TiN or SiN) same (substrate or wafer)) and ((metal\$4 or conductive or wir\$3) same (pattern or cavity or line)) and ((develop\$4 or strip\$4 or remov\$3) same (polymer or photoresist or resist or polyimide or polyamide)))	US-PGPUB